TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

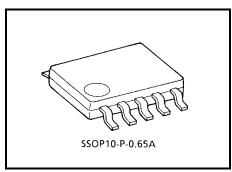
TA6009FN,TA6009FNG

Shock Sensor IC (1 ch version)

TA6009FN/FNG detects an existence of external shock through the shock sensor and output.

Features

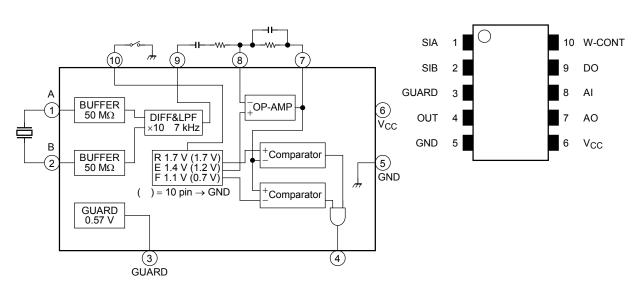
- $\bullet~$ TA6009FN/FNG operates from 2.7 to 5.5 V DC single power supply voltage.
- Signal from the shock sensor is amplified according to setting gain, and is detected through the internal window comparator.
- TA6009FN/FNG incorporates 1-ch shock detecting circuitry.
- Input terminal of sensor signal is designed high impedance. Differential input impedance = $100 \text{ M}\Omega$ (typ.)
- LPF (low pass filter) circuitry is incorporated. Cut-off frequency of LPF = 7 kHz
- · Sensitivity of shock detection can be adjusted by external devices.
- Small package SSOP10-P-0.65A (0.65 mm pitch)



Weight: 0.04 g (typ.)

Block Diagram

Pin Connection (top view)



Pin Function

Pin No.	Pin Name	Function
1	SIA	Connection terminal of shock sensor
2	SIB	Connection terminal of shock sensor
3	GUARD	Input (1, 2 pin) GUARD terminal
4	OUT	Output terminal (output = "L" when shock is detected.)
5	GND	Ground terminal
6	V _{CC}	Power supply voltage
7	AO	Op-Amp output terminal
8	Al	Op-Amp input terminal
9	DO	Differential-Amp output terminal
10	W-CONT	WindComp. trip voltage selection terminal

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	7	V
Power dissipation	P_{D}	300	mW
Storage temperature	T _{stg}	-55 to 150	°C

Recommend Operating Condition

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	2.7 to 5.5	٧	
Operating temperature	T _{opr}	–25 to 85	°C	

Electrical Characteristics (unless otherwise specified, $V_{CC} = 3.3 \text{ V}$, $Ta = 25^{\circ}\text{C}$)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Supply voltage	V _{CC}	_	_	2.7	3.3	5.5	V
Cupply current	laa	(1)	V _{CC} = 3.3 V		1.8	2.4	mΛ
Supply current	ICC	(1)		2.4	- mA		

(GUARD)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Output voltage	VoGur	(2)	_	0.52	0.57	0.62	٧

(DIFF-AMP)

Characteristics		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input impedance	(Note 1)	Zin	_			100		МΩ
Gain		GvBuf	(3)	_	19.6	20	20.4	dB
Output DC voltage		VoBuf	(4)	Connect C = 100 pF between 1 pin and 2 pin	0.7	1	1.3	٧
Low pass filter cut-off freq.		fc	(5)	Frequency at -3dB point	5	7	10	kHz
Output source current		IBso	(6)	Voh = V _{CC} – 1 V	400	800		μА
Output sink current		IBsi	(7)	Vol = 0.3 V	75	130		μΑ

Note 1: Marked parameters are reference data.

(OP-AMP)

Characteristics		Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
Cut-off frequency	(Note 1)	fT	_	_	_		2		MHz
Openloop gain	(Note 1)	Gvo	_	_		80	90		dB
Input voltage 1		Vin1	(8)	10 pin → OPEN (Note 2)		1.33	1.4	1.47	V
Input voltage 2		Vin2	(9)	10 pin \rightarrow GND (Note 2)		1.14	1.2	1.26	V
Input current		l _{in}	(10)	_			25	50	nA
Offset voltage	(Note 1)	Voff	_	_		-5	0	5	mV
Output source current		IAso	(11)	Voh = V _{CC} – 1 V		300	800		μА
Output sink current		IAsi	(12)	Vol = 0.3 V		130	200		μА

Note 1: Marked parameters are reference data.

(window-comparator)

Characteristics		Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
Trip voltage 1	(Note 1)	Vtrp1	_	10 pin → OPEN	(Note 2)	Vin1 ±0.285	Vin1 ±0.3	Vin1 ±0.315	٧
Trip voltage 2	(Note 1)	Vtrp2	_	10 pin → GND	(Note 2)	Vin2 ±0.475	Vin2 ±0.5	Vin2 ±0.525	٧
Output source current		IWso	(13)	$Voh = V_{CC} - 0.5 V$		30	50		μА
Output sink current		IWsi	(14)	Vol = 0.3 V		300	800		μА

Note 1: Marked parameters are reference data.

Note 2: 10 pin must be non-connected otherwise connected to GND.

Note 2: 10 pin must be non-connected otherwise connected to GND.



Application Note

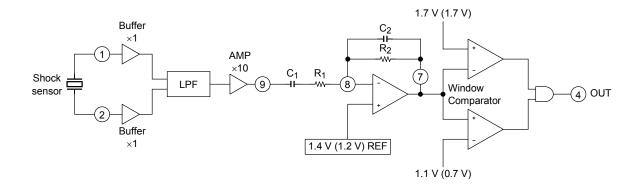


Figure 1 The Composition of G-Force Sense Amplifier

Figure 1 is the composition of G-Force sense amplifier.

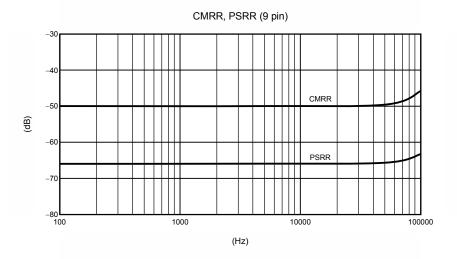
The shock sensor is connected between 1 and 2 terminal.

When G-force Sensor (sensor sensibility = s (mV/G)) is used to detect external shock of g (G), the external parts are determined as following.

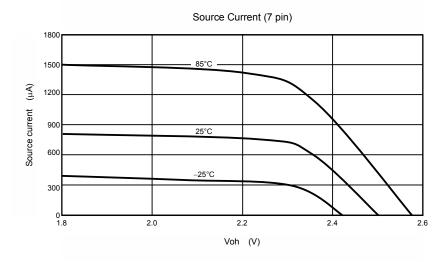
```
\begin{split} &(\text{gain setting})*10 \text{ PIN} \rightarrow \text{GND} \\ &500/(s \times g) = G1 \\ &G1/10 = G \text{ (OP-AMP)} \\ &(\text{HPF setting}) \\ &\text{fc} = 1/(2 \ \pi \times R_1 \times C_1) \\ &(\text{LPF setting}) \\ &\text{fc} = 1/(2 \ \pi \times R_2 \times C_2) \end{split}
```

Reference Data

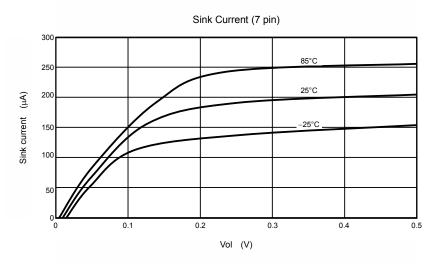
(1) 9 pin (DIFF-AMP output) CMRR, PSRR



(2) 7 pin (OP-AMP output) source current

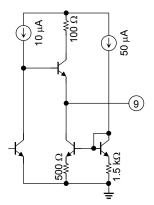


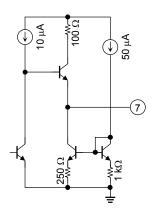
(3) 7 pin (OP-AMP output) sink current

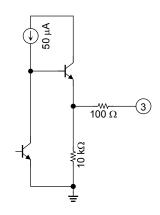


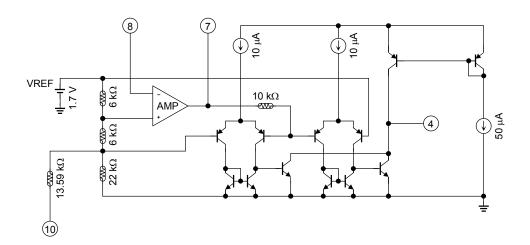


Equivalent Circuit





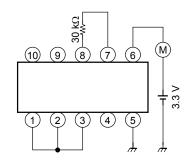




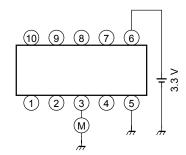
6 2003-12-03

Test Circuit

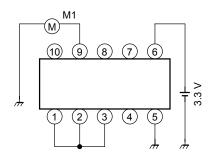
(1) Supply current ICC



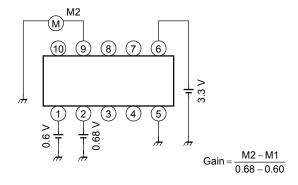
(2) GUARD Output voltage **VoGur**



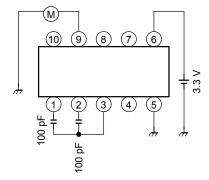
(3) DIFF-AMP Gain **GvBuf** Step 1



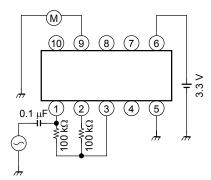
Step 2



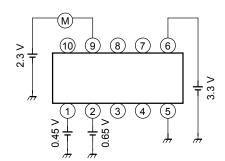
(4) DIFF-AMP Output DC voltage **VoBuf**



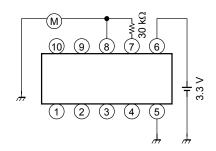
(5) DIFF-AMP
Low pass filter cut-off freq. **fc**



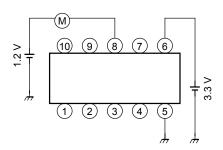
(6) DIFF-AMP
Output source current **IBso**



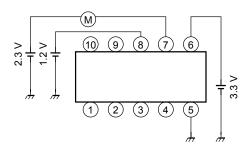
(8) OP-AMP Input voltage 1 **Vin1**



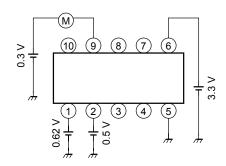
(10) OP-AMP Input current **I**in



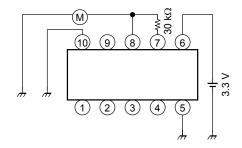
(11) OP-AMP Output source current **IAso**



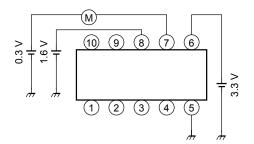
(7) DIFF-AMP Output sink current **IBsi**



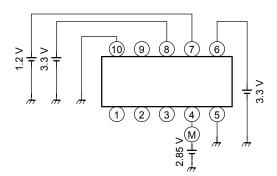
(9) OP-AMP Input voltage 2 **Vin2**



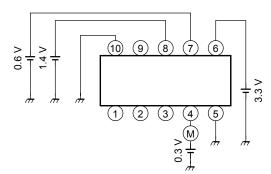
(12) OP-AMP Output sink current **IAsi**



(13) Window comparator Output source current **IWso**

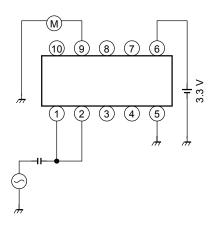


(14) Window comparator Output sink current **IWsi**

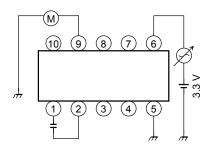


Test Circuit (for reference)

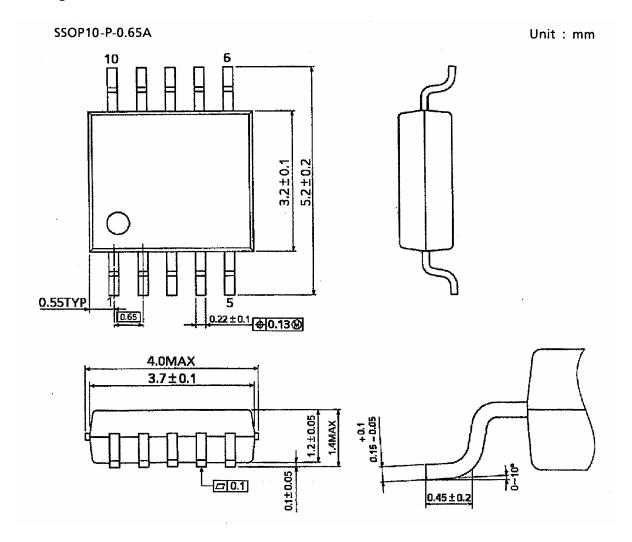
(a) DIFF-AMP **CMRR**



(b) DIFF-AMP **PSRR**



Package Dimensions



Weight: 0.04 g (typ.)

RESTRICTIONS ON PRODUCT USE

030619EAA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
 may result from its use. No license is granted by implication or otherwise under any patent or patent rights of
 TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.